



- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

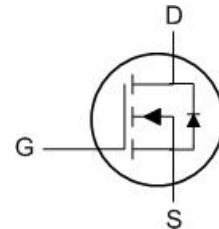
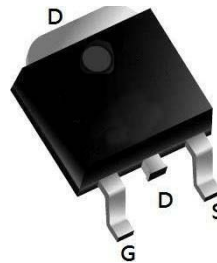
**Product Summary**

| BVDSS | RDSON | ID  |
|-------|-------|-----|
| 100V  | 25mΩ  | 40A |

**Description**

The XXW40N10 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XXW40N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

**TO252 Pin Configuration**

**Absolute Maximum Ratings** ( $T_C=25^{\circ}\text{C}$  unless otherwise specified)

| Symbol          | Parameter                                       | Max.                        | Units                       |
|-----------------|-------------------------------------------------|-----------------------------|-----------------------------|
| $V_{DSS}$       | Drain-Source Voltage                            | 100                         | V                           |
| $V_{GSS}$       | Gate-Source Voltage                             | $\pm 20$                    | V                           |
| $I_D$           | Continuous Drain Current                        | $T_C = 25^{\circ}\text{C}$  | 40                          |
|                 |                                                 | $T_C = 100^{\circ}\text{C}$ | 21                          |
| $I_{DM}$        | Pulsed Drain Current <sup>note1</sup>           | 120                         | A                           |
| EAS             | Single Pulsed Avalanche Energy <sup>note2</sup> | 30                          | mJ                          |
| $P_D$           | Power Dissipation                               | $T_C = 25^{\circ}\text{C}$  | 42                          |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case            | 3.6                         | $^{\circ}\text{C}/\text{W}$ |
| $T_J, T_{STG}$  | Operating and Storage Temperature Range         | -55 to +175                 | $^{\circ}\text{C}$          |

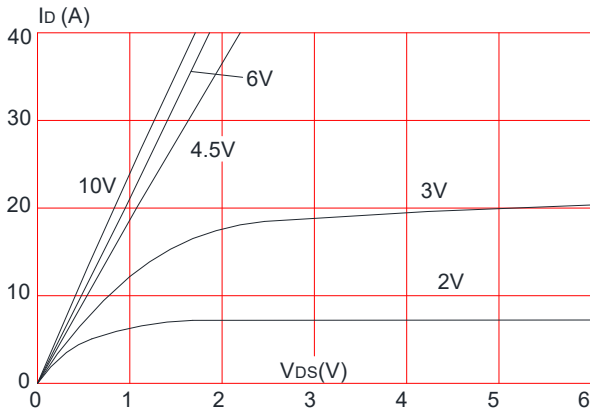
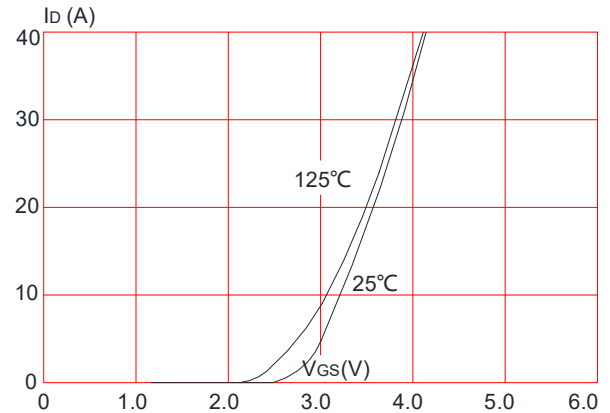
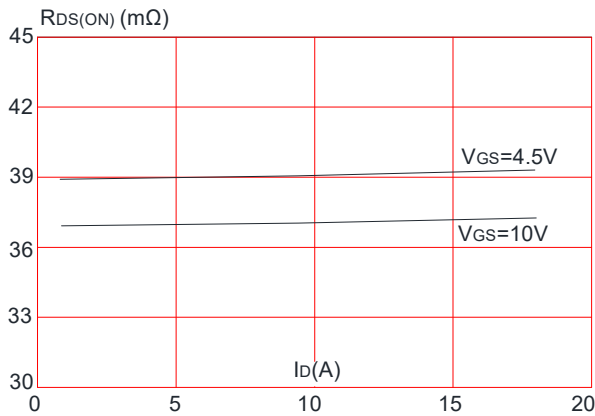
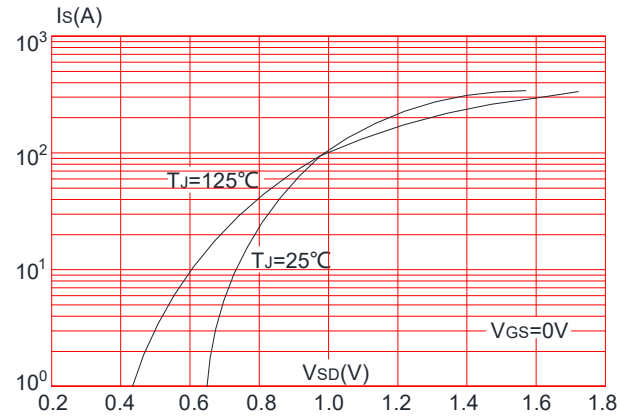
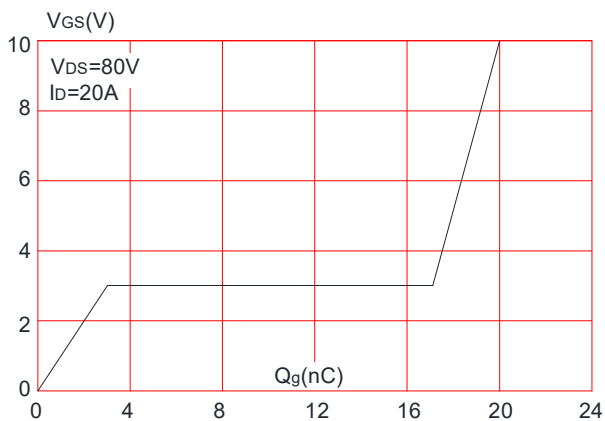
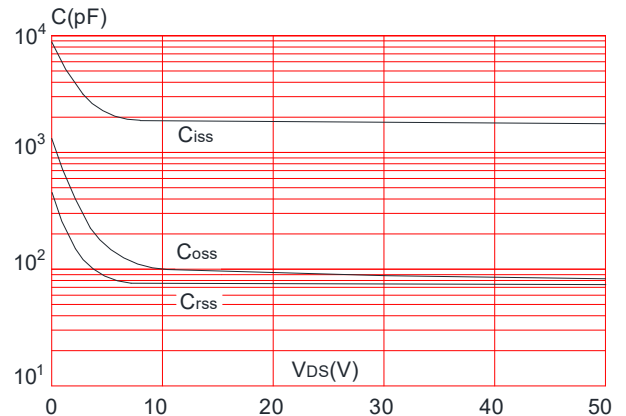
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

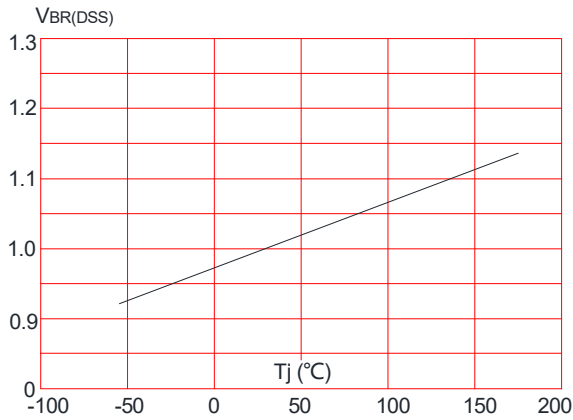
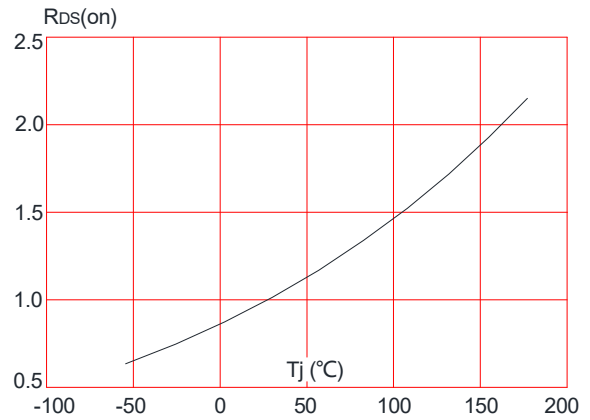
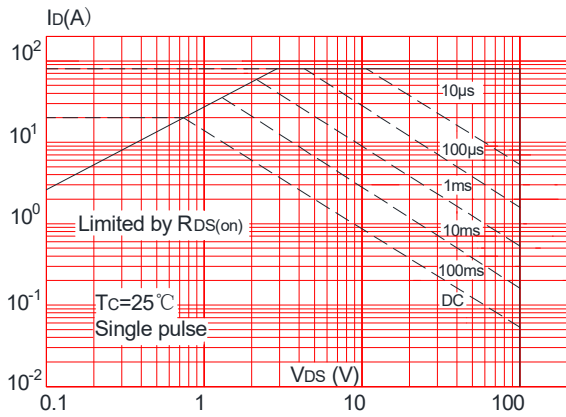
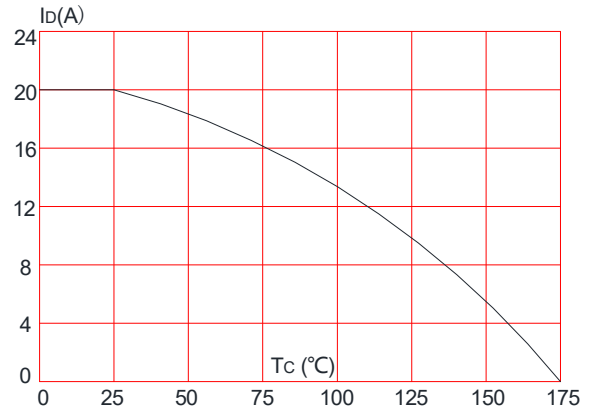
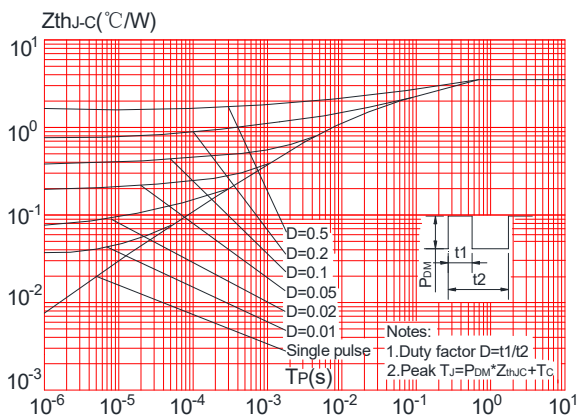
| Symbol                                                        | Parameter                                                 | Test Condition                                         | Min. | Typ. | Max.      | Units      |
|---------------------------------------------------------------|-----------------------------------------------------------|--------------------------------------------------------|------|------|-----------|------------|
| <b>Off Characteristic</b>                                     |                                                           |                                                        |      |      |           |            |
| $V_{(BR)DSS}$                                                 | Drain-Source Breakdown Voltage                            | $V_{GS}=0V, I_D=250\mu A$                              | 100  | -    | -         | V          |
| $I_{DSS}$                                                     | Zero Gate Voltage Drain Current                           | $V_{DS}=100V, V_{GS}=0V,$                              | -    | -    | 1.0       | $\mu A$    |
| $I_{GSS}$                                                     | Gate to Body Leakage Current                              | $V_{DS}=0V, V_{GS}=\pm 20V$                            | -    | -    | $\pm 100$ | nA         |
| <b>On Characteristics</b>                                     |                                                           |                                                        |      |      |           |            |
| $V_{GS(th)}$                                                  | Gate Threshold Voltage                                    | $V_{DS}=V_{GS}, I_D=250\mu A$                          | 1.0  | 1.5  | 2.2       | V          |
| $R_{DS(on)}$                                                  | Static Drain-Source on-Resistance<br><small>note3</small> | $V_{GS}=10V, I_D=10A$                                  | -    | 25   | 32.5      | m $\Omega$ |
|                                                               |                                                           | $V_{GS}=4.5V, I_D=6A$                                  | -    | 26   | 36        | m $\Omega$ |
| <b>Dynamic Characteristics</b>                                |                                                           |                                                        |      |      |           |            |
| $C_{iss}$                                                     | Input Capacitance                                         | $V_{DS}=25V, V_{GS}=0V,$<br>$f=1.0MHz$                 | -    | 1964 | -         | pF         |
| $C_{oss}$                                                     | Output Capacitance                                        |                                                        | -    | 90   | -         | pF         |
| $C_{rss}$                                                     | Reverse Transfer Capacitance                              |                                                        | -    | 74   | -         | pF         |
| $Q_g$                                                         | Total Gate Charge                                         | $V_{DS}=80V, I_D=20A,$<br>$V_{GS}=4.5V$                | -    | 20   | -         | nC         |
| $Q_{gs}$                                                      | Gate-Source Charge                                        |                                                        | -    | 3.1  | -         | nC         |
| $Q_{gd}$                                                      | Gate-Drain("Miller") Charge                               |                                                        | -    | 14   | -         | nC         |
| <b>Switching Characteristics</b>                              |                                                           |                                                        |      |      |           |            |
| $t_{d(on)}$                                                   | Turn-on Delay Time                                        | $V_{DS}=80V, I_D=20A,$<br>$R_G=3.1\Omega, V_{GS}=4.5V$ | -    | 11   | -         | ns         |
| $t_r$                                                         | Turn-on Rise Time                                         |                                                        | -    | 91   | -         | ns         |
| $t_{d(off)}$                                                  | Turn-off Delay Time                                       |                                                        | -    | 40   | -         | ns         |
| $t_f$                                                         | Turn-off Fall Time                                        |                                                        | -    | 71   | -         | ns         |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |                                                           |                                                        |      |      |           |            |
| $I_S$                                                         | Maximum Continuous Drain to Source Diode Forward Current  |                                                        | -    | -    | 40        | A          |
| $I_{SM}$                                                      | Maximum Pulsed Drain to Source Diode Forward Current      |                                                        | -    | -    | 120       | A          |
| $V_{SD}$                                                      | Drain to Source Diode Forward Voltage                     | $V_{GS}=0V, I_S=20A$                                   | -    | -    | 1.2       | V          |
| $t_{rr}$                                                      | Body Diode Reverse Recovery Time                          | $I_F=20A,$<br>$di/dt=100A/\mu s$                       | -    | 64   | -         | ns         |
| $Q_{rr}$                                                      | Body Diode Reverse Recovery Charge                        |                                                        | -    | 152  | -         | nC         |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

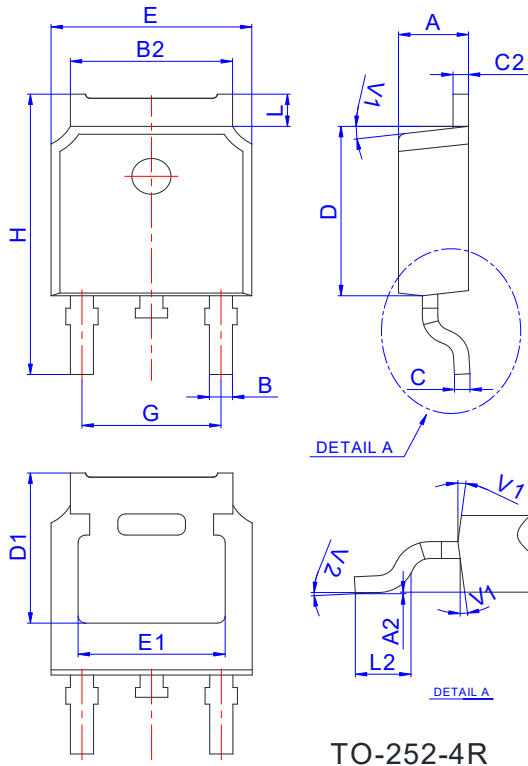
2. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}= 11A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

**Typical Performance Characteristics**
**Figure 1: Output Characteristics**

**Figure 2: Typical Transfer Characteristics**

**Figure 3: On-resistance vs. Drain Current**

**Figure 4: Body Diode Characteristics**

**Figure 5: Gate Charge Characteristics**

**Figure 6: Capacitance Characteristics**


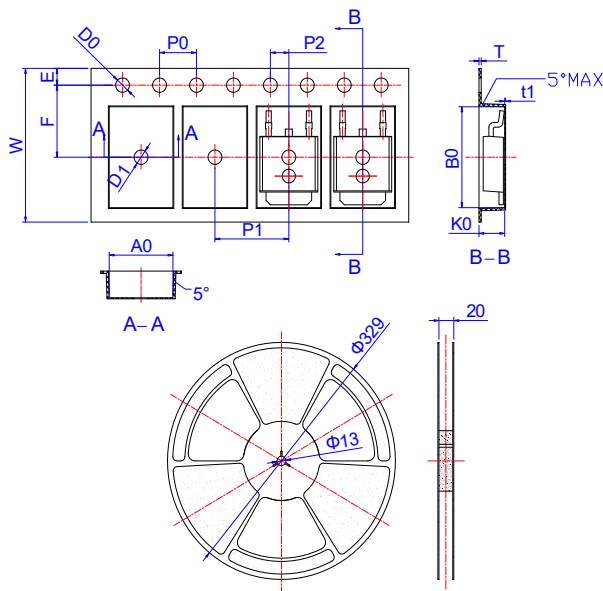
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

**Figure 8:** Normalized on Resistance vs. Junction Temperature

**Figure 9:** Maximum Safe Operating Area

**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case


### Package Mechanical Data-TO-252-4R



| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

### Reel Specification-TO-252-4R



| Ref. | Dimensions  |       |       |        |       |       |
|------|-------------|-------|-------|--------|-------|-------|
|      | Millimeters |       |       | Inches |       |       |
|      | Min.        | Typ.  | Max.  | Min.   | Typ.  | Max.  |
| W    | 15.90       | 16.00 | 16.10 | 0.626  | 0.630 | 0.634 |
| E    | 1.65        | 1.75  | 1.85  | 0.065  | 0.069 | 0.073 |
| F    | 7.40        | 7.50  | 7.60  | 0.291  | 0.295 | 0.299 |
| D0   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| D1   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| P0   | 3.90        | 4.00  | 4.10  | 0.154  | 0.157 | 0.161 |
| P1   | 7.90        | 8.00  | 8.10  | 0.311  | 0.315 | 0.319 |
| P2   | 1.90        | 2.00  | 2.10  | 0.075  | 0.079 | 0.083 |
| A0   | 6.85        | 6.90  | 7.00  | 0.270  | 0.271 | 0.276 |
| B0   | 10.45       | 10.50 | 10.60 | 0.411  | 0.413 | 0.417 |
| K0   | 2.68        | 2.78  | 2.88  | 0.105  | 0.109 | 0.113 |
| T    | 0.24        |       | 0.27  | 0.009  |       | 0.011 |
| t1   | 0.10        |       |       | 0.004  |       |       |
| 10P0 | 39.80       | 40.00 | 40.20 | 1.567  | 1.575 | 1.583 |